

IN THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1-5. (canceled).

6. (Currently amended) A method of manufacturing a light-emitting device, comprising: discharging liquid comprising an organic light-emitting material to a pixel column over a substrate from a nozzle by contacting a contact element attached to the nozzle to a bank so that the nozzle contact element and the pixel column are connected through the liquid comprising said organic light-emitting material,

wherein the nozzle is provided with the contact element through which the liquid is discharged.

7. (Previously presented) A method of manufacturing a light-emitting device according to claim 6, wherein said nozzle has a large internal diameter portion and a small internal diameter portion.

8-18. (Canceled)

19. (Previously presented) A method of manufacturing a light-emitting device according to claim 6, further comprising forming a pixel electrode over the substrate.

20-25. (Canceled)

26. (Previously presented) A method of manufacturing a light-emitting device according to claim 6, further comprising:

forming a thin film transistor over the substrate;

forming an insulating film over said thin film transistor.

27-30. (Canceled)

31. (Previously presented) A method of manufacturing a light-emitting device according to claim 6,

wherein said liquid comprising said organic light-emitting material is discharged with scanning the nozzle along a direction parallel to the pixel column .

32-47. (Canceled).

48. (Previously presented) A method of manufacturing a light-emitting device according to claim 6, wherein ultrasonic oscillation is applied to the liquid comprising the organic light-emitting material when the liquid is discharged from the nozzle.

49. (Previously presented) A method of manufacturing a light-emitting device according to

claim 6, wherein the liquid comprising the organic light-emitting material is heated when the liquid is discharged from the nozzle.

50. (Currently amended) A method of manufacturing a light-emitting device according to claim 6, wherein the bank comprises a resin material.

51.(Currently amended) A method of manufacturing a light-emitting device according to claim 19, wherein the bank covers an edge portion of the pixel electrode.

52. (Canceled)

53. (New) A method of manufacturing a light-emitting device, comprising:
discharging liquid comprising a light-emitting material to a pixel column over a substrate from a nozzle by contacting a contact element attached to the nozzle to a bank so that the contact element and the pixel column are connected through the liquid comprising said light-emitting material,

wherein the nozzle is provided with the contact element through which the liquid is discharged.

54. (New) A method of manufacturing a light-emitting device according to claim 53, wherein said nozzle has a large internal diameter portion and a small internal diameter portion.

55. (New) A method of manufacturing a light-emitting device according to claim 53, further comprising forming a pixel electrode over the substrate.

56. (New) A method of manufacturing a light-emitting device according to claim 53, further comprising:

forming a thin film transistor over the substrate;

forming an insulating film over said thin film transistor.

57. (New) A method of manufacturing a light-emitting device according to claim 53, wherein said liquid comprising said light-emitting material is discharged with scanning the nozzle along a direction parallel to the pixel column .

58. (New) A method of manufacturing a light-emitting device according to claim 53, wherein ultrasonic oscillation is applied to the liquid comprising the light-emitting material when the liquid is discharged from the nozzle.

59. (New) A method of manufacturing a light-emitting device according to claim 53, wherein the liquid comprising the light-emitting material is heated when the liquid is discharged from the nozzle.

60. (New) A method of manufacturing a light-emitting device according to claim 53, wherein the bank comprises a resin material.

61. (New) A method of manufacturing a light-emitting device according to claim 53, wherein the bank covers an edge portion of the pixel electrode.

62. (New) A method manufacturing a light-emitting device according to claim 6, wherein the light-emitting device is a passive type.

63. (New) A method manufacturing a light-emitting device according to claim 53, wherein the light-emitting device is a passive type.

64. (New) A method of manufacturing an active matrix type light-emitting device, comprising:

forming a pixel column comprising a plurality of pixel electrodes and a plurality of thin film transistors,

discharging liquid comprising an organic light-emitting material to the pixel column over a substrate from a nozzle by contacting a contact element attached to the nozzle to a bank so that the contact element and the pixel column are connected through the liquid comprising said organic light-emitting material,

wherein the nozzle is provided with the contact element through which the liquid is discharged.

65. (New) A method of manufacturing an active matrix type light-emitting device

according to claim 64, wherein said nozzle has a large internal diameter portion and a small internal diameter portion.

66. (New) A method of manufacturing an active matrix type light-emitting device according to claim 64,

wherein said liquid comprising said organic light-emitting material is discharged with scanning the nozzle along a direction parallel to the pixel column .

67. (New) A method of manufacturing an active matrix type light-emitting device according to claim 64, wherein ultrasonic oscillation is applied to the liquid comprising the organic light-emitting material when the liquid is discharged from the nozzle.

68. (New) A method of manufacturing an active matrix type light-emitting device according to claim 64, wherein the liquid comprising the organic light-emitting material is heated when the liquid is discharged from the nozzle.

69. (New) A method manufacturing an active matrix type light-emitting device according to claim 64, wherein the bank comprises a resin material.

70. (New) A method manufacturing an active matrix type light-emitting device according to claim 64, wherein the bank covers an edge portion of the pixel electrode.

71. (New) A method of manufacturing an active matrix type light-emitting device, comprising:

forming a pixel column comprising a plurality of pixel electrodes and a plurality of thin film transistors,

discharging liquid comprising a light-emitting material to the pixel column over a substrate from a nozzle by contacting a contact element attached to the nozzle to a bank so that the contact element and the pixel column are connected through the liquid comprising said light-emitting material,

wherein the nozzle is provided with the contact element through which the liquid is discharged.

72. (New) A method of manufacturing an active matrix type light-emitting device according to claim 71, wherein said nozzle has a large internal diameter portion and a small internal diameter portion.

73. (New) A method of manufacturing an active matrix type light-emitting device according to claim 71,

wherein said liquid comprising said light-emitting material is discharged with scanning the nozzle along a direction parallel to the pixel column .

74. (New) A method of manufacturing an active matrix type light-emitting device according to claim 71, wherein ultrasonic oscillation is applied to the liquid comprising the

light-emitting material when the liquid is discharged from the nozzle.

75. (New) A method of manufacturing an active matrix type light-emitting device according to claim 71, wherein the liquid comprising the light-emitting material is heated when the liquid is discharged from the nozzle.

76. (New) A method manufacturing an active matrix type light-emitting device according to claim 71, wherein the bank comprises a resin material.

77. (New) A method manufacturing an active matrix type light-emitting device according to claim 71, wherein the bank covers an edge portion of the pixel electrode.